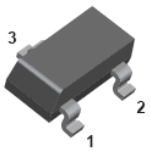
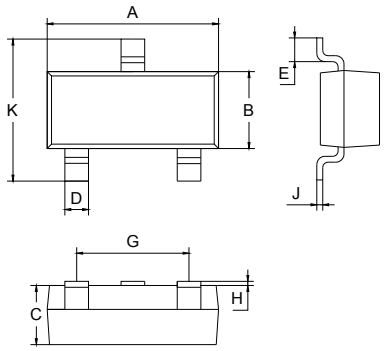
KTD1304
NPN Silicon Epitaxial Planar Transistor

RoHS COMPLIANT





SOT-23		
Dim	Min	Max
A	2.70	3.10
B	1.10	1.50
C	1.0 Typical	
D	0.4 Typical	
E	0.35	0.48
G	1.80	2.00
H	0.02	0.1
J	0.1 Typical	
K	2.20	2.60
All Dimensions in mm		

FEATURES

- High emitter-base voltage.
- High reverse h_{FE}.
- Low on resistance.

APPLICATIONS

- Audio muting application.

ORDERING INFORMATION

Type No.	Marking	Package Code
KTD1304	MAX	SOT-23

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	25	V
V_{CEO}	Collector-Emitter Voltage	20	V
V_{EBO}	Emitter-Base Voltage	12	V
I_C	Collector Current -Continuous	300	mA
I_B	Base Current	30	mA
P_C	Collector Power Dissipation	200	mW
T_j,T_{stg}	Junction and Storage Temperature	-55 to +150	℃

ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA,I_E=0	25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA,I_C=0	12			V
Collector cut-off current	I_{CBO}	V_{CB}=25V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=12V,I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=2V,I_C=4mA	200		800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=100mA, I_B=10mA			0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=100mA, I_B=10mA			1	V
Transition frequency	f_T	V_{CE}=10V, I_C= 1mA		60		MHz
Collector output capacitance	C_{ob}	V_{CB}=10V,I_E=0,f=1MHz			10	pF

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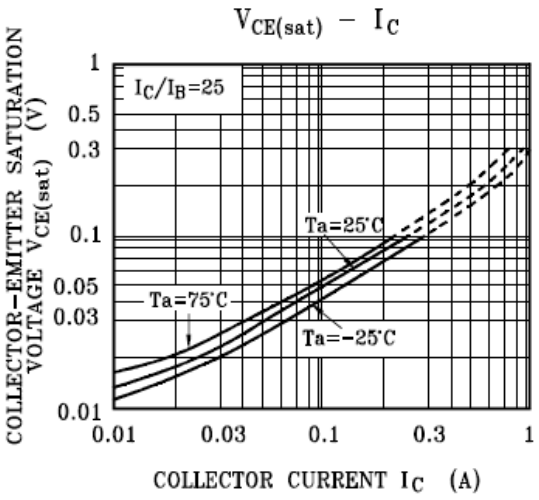
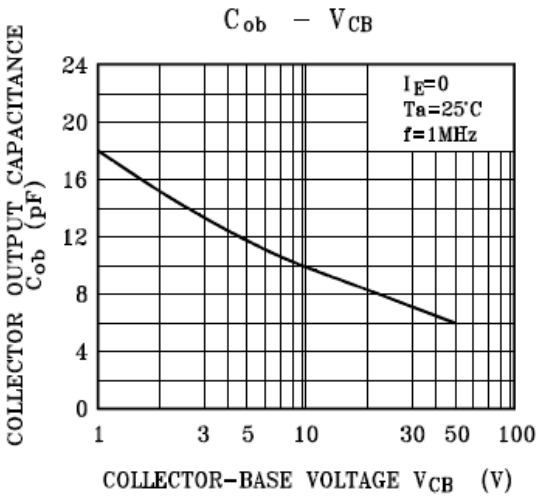
TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified





Device	Package	Shipping
KTD1304	SOT-23	3000/Tape&Reel